

AMENDMENTS TO THE CLAIMS

Please amend the claims as follows:

Listing of Claims:

Claims 1-31 (Canceled).

Claim 32 (Previously Presented): A semiconductor chip, comprising:

 a base substrate;

 a bulk device region having a bulk growth layer on a part of the base substrate, the bulk device region having a first device-fabrication surface in which a bulk device is positioned on the bulk growth layer;

 a pn junction formed in the bulk device region and positioned above an interface between the base substrate and the bulk growth layer;

 an SOI device region having a buried insulator on the other part of the base substrate and an SOI layer on the buried insulator, the SOI device region having a second device-fabrication surface in which an SOI device is positioned on the SOI layer, the first and second device-fabrication surface being positioned at a substantially uniform level;

 a first isolation formed in the bulk device region so as to separate the bulk device, and a second isolation in the SOI device region so as to separate the SOI device, the first and second isolations being substantially the same depth and having a depth reaching the buried insulator;

 a boundary layer located at a boundary between the bulk device region and the SOI device region; and

 a dummy trench in the bulk device region between the bulk device and the SOI device.

Claim 33 (Previously Presented): The semiconductor chip according to claim 32, wherein the dummy trench is deeper than the buried insulator.

Claim 34 (Previously Presented): The semiconductor chip according to claim 32, wherein the bulk device positioned in the bulk device region includes a DRAM cell having a trench capacitor, and the dummy trench is a dummy capacitor.

Claim 35 (Previously Presented): A semiconductor chip comprising:

- a base substrate;
- a bulk device region having a bulk growth layer on a part of the base substrate, the bulk device region having a first device-fabrication surface in which a bulk device is positioned on the bulk growth layer;
- an SOI device region having a buried insulator on the other part of the base substrate and an SOI layer on the buried insulator, the SOI device region having a second device-fabrication surface in which an SOI device is positioned on the SOI layer, the first and second device-fabrication surface being positioned at a substantially uniform level;
- a boundary layer located at a boundary between the bulk device region and the SOI device region; and
- a dummy trench formed in the bulk device region between the bulk device and the SOI device.

Claim 36 (Previously Presented): The semiconductor chip according to claim 35, wherein the dummy trench is a dummy capacitor.

Claim 37 (Previously Presented): The semiconductor chip according to claim 35, wherein the dummy trench is deeper than the buried insulator.

Claim 38 (Previously Presented): The semiconductor chip according to claim 35, wherein the bulk device positioned in the bulk device region includes a vertical bipolar transistor having an isolation trench, the isolation trench functioning as the dummy trench.

Claim 39 (Previously Presented): The semiconductor chip according to claim 35, wherein the bulk device positioned in the bulk device region includes a DRAM cell having a trench capacitor.

Claim 40 (Previously Presented): The semiconductor chip according to claim 35, wherein the bulk device positioned in the bulk device region includes a DRAM cell having a trench capacitor and a MOSFET, wherein the MOSFET is positioned between the DRAM cell and the dummy trench.

Claim 41 (Previously Presented): The semiconductor chip according to claim 35, wherein the bulk growth layer is a silicon bulk growth layer, and the boundary layer reaches the base substrate and is made of one of polysilicon or silicon-based compound semiconductors.

Claim 42 (Previously Presented): The semiconductor chip according to claim 35, wherein the bulk device region includes a first isolation separating the bulk device, and the SOI device region includes a second isolation separating the SOI device, the first and second isolations being of substantially the same depth.

Claim 43 (Previously Presented): The semiconductor chip according to claim 42, wherein the first and second isolations have a depth reaching the buried insulator.

Claim 44 (Previously Presented): The semiconductor chip according to claim 43, wherein the bulk device region has a pn junction positioned above an interface between the base substrate and the bulk growth layer.

Claim 45 (Previously Presented): The semiconductor chip according to claim 35, further comprising a first isolation in the bulk device region, a second isolation in the SOI device region, and a third isolation positioned at the boundary and functioning as the boundary layer, wherein the first, second, and third isolations are of substantially the same depth.

Claim 46 (Previously Presented): The semiconductor chip according to claim 45, wherein the first, second, and third isolations are deeper than the buried insulator.

Claim 47 (Previously Presented): The semiconductor chip according to claim 46, wherein the third isolation has a sidewall that is in contact with the buried insulator.

Claim 48 (Previously Presented): The semiconductor chip according to claim 35, further comprising a first isolation in the bulk device region, a second isolation in the SOI device region, and a third isolation positioned at the boundary and functioning as the boundary layer, wherein the second isolation is shallower than the third isolation.